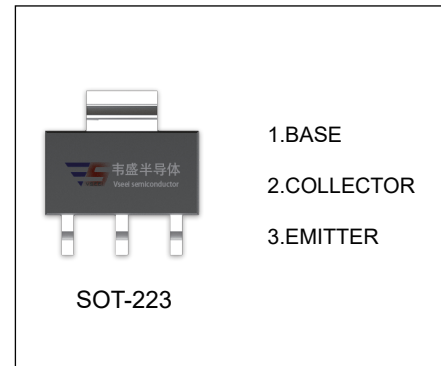


CZT122 TRANSISTOR (NPN)

FEATURES

- Complementary to CZT127
- Silicon Power Darlington Transistors
- Low speed switching and amplifier applications



MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	100	V
V _{CEO}	Collector-Emitter Voltage	100	V
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current -Continuous	5	A
P _C	Collector Power Dissipation	1	W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~150	°C

ELECTRICAL CHARACTERISTICS (T_a=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =1mA, I _E =0	100			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C =30mA, I _B =0	100			V
Collector cut-off current	I _{CBO}	V _{CB} =100V, I _E =0			200	uA
Base cut-off current	I _{CEO}	V _{CE} =50V, I _B =0			500	uA
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _C =0			2	mA
DC current gain	h _{FE(1)}	V _{CE} =3V, I _C =0.5A	1000			
	h _{FE(2)}	V _{CE} =3V, I _C =3A	1000			
Collector-emitter saturation voltage	V _{CE(sat)1}	I _C =3A, I _B =12mA			2	V
	V _{CE(sat)2}	I _C =5A, I _B =20mA			4	V
Base-emitter voltage	V _{BE(on)}	V _{CE} =3V, I _C =3A			2.5	V
Transition frequency	f _T	V _{CE} =4V, I _C =3A, f=1MHz	4			MHz
Collector output capacitance	C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz			200	pF

Typical Characteristics

CZT122

